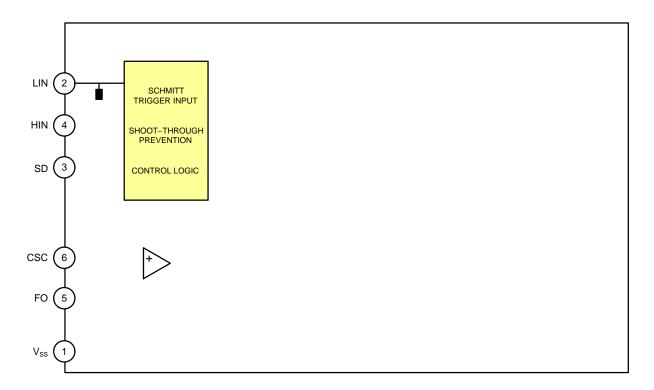


BLOCK DIAGRAM



SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS (T_A = 25 C, unless dtherwise specified.)

Symbol	Rating		Value	Unit
VS	High-side Offset Voltage V _S		$(V_{B} - 25)$ to $(V_{B} + 0.3)$	V
VB	High-side Floating Supply Voltage V _B		-0.3 to 1225	V
V _{HO}	High-side Floating Output Voltage		$(V_{S} - 0.3)$ to $(V_{B} + 0.3)$	V
V _{DD}	Low-side and Logic-fixed Supply Voltage		-0.3 to 25	V
V _{IN}	Logic Input Voltage (HIN, LIN, SD)		–0.3 to (V _{DD} + 0.3)	V
V _{CSC}	Current Sense Input Voltage		–0.3 to (V _{DD} + 0.3)	V
dV _S /dt	Allowable Offset Voltage Slew Rate		50	V/ns
PD	Power Dissipation (SO14NB) (Note 1)		0.8	W
JA	Thermal Resistance, Junction-to-Ambient (S	SO14NB)	156	C/W
T _{J(max)}	Junction Temperature		+150	С
TSTG	Storage Temperature		-55 to +150	С
ESDHBM	ESD, Human Body Model (Note 3)		2500	V
ESDCDM	ESD, Charged Device Model (Note 3)		750	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Do not exceed PD under any circumstances.

Do not exceed PD under any circumstances.
 Mounted on 76.2 114.3 1.6 mm PCB (FR-4 glass epoxy material). Refer to the following standards:

 JESD51-2: Integral circuits thermal test method environmental conditions – natural convection
 JESD51-3: Low effective thermal conductivity test boars for leaded surface mount packages

 This device series incorporates ESD protection and is test of by the following methods:

 ESD Human Body Model tested per ANSI/ESDA/JEDE0 JS-001-2012
 ESD Charged Davies Model tested per LESD22 C101

- ESD Charged Device Model tested per JESD22-C101

RECOMMENDED OPERATING RANGES (Parameters are referenced to V_{SS})

	II	11			
Symbol	Rating		Min	Max	Unit
V _{DD}	Supply Voltage Range		4.5	18.0	V
VS	High-Side V _S Floating Supply Offset Volt	ge (Note 4)	5 – V _{BS}	1200	V
V _{BS}	High-side V _{BS} Bootstrap Voltage		V _{BSUV+}	22	V
V _{HO}	High-Side Output Voltage		V _S	V _B	V
V _{DD}	Low-Side and Logic Supply Voltage		V _{DDUV+}	22	V

 V_{h}

ELECTRICAL CHARACTERISTICS

 $(V_{BIAS} (V_{DD}, V_{BS}) = 15 \text{ V}, T_A = -40 \text{ C}$ to 125 C unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to V

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{BIAS} (V_{DD}, V_{BS}) = 15 \text{ V}, \text{ T}_{A} = -40 \text{ C}$ to 125 C unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to V_{SS} . The V_{O} and I_{O} parameters are referenced to V_{S} and COM and are applicable to the respective outputs HO and LO.)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
FAULT DETE	CTION SECTION					
V _{FOH}	Fault Output High Level Voltage	V_{CSC} = 0 V, $R_{PULL-UP}$ = 4.7 k Ω	4.7	-	-	V
V _{FOL}	Fault Output Low Level Voltage	$V_{CSC} = 1 \text{ V}, I_{FO} = 2 \text{ mA}$	-	-	0.8	V

DYNAMIC OUTPUT SECTION

 $(V_{BIAS} (V_{DD}, V_{BS}) = 15.0 \text{ V}, T_A = -40 \text{ C}$ to 125

TYPICAL CHARACTERISTICS (Continued)

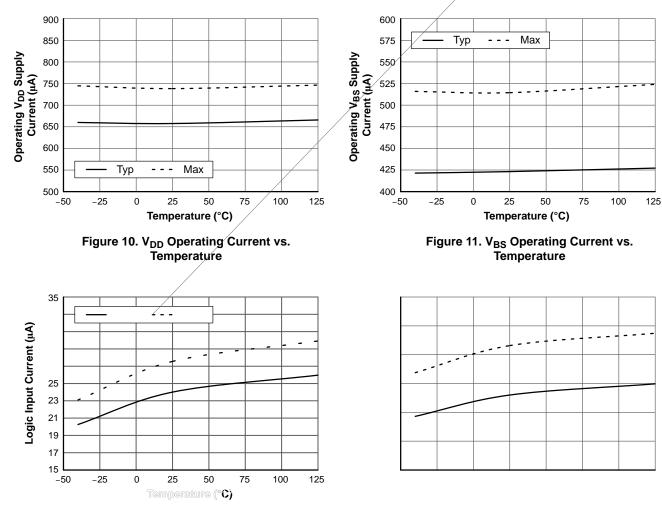


Figure 12. Logic High Input Bias Current vs. Temperature

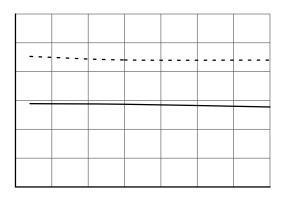


Figure 14. I_{SOFT} vs. Temperature

Figure 13. I_{CSCIN} vs. Temperature

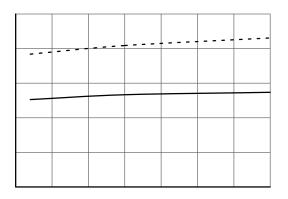
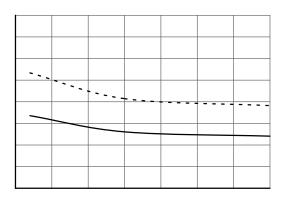
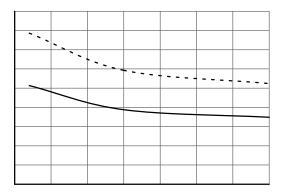


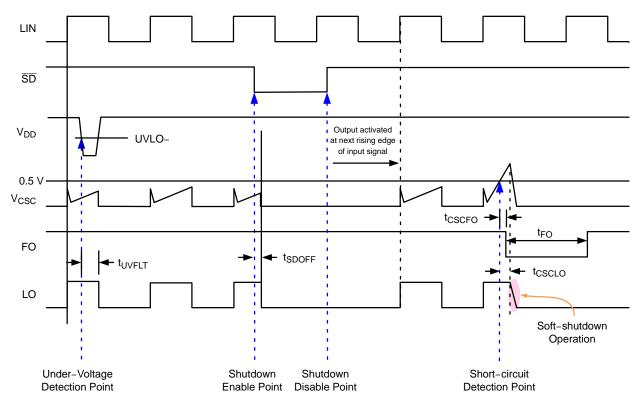
Figure 15. Turn-on Rising Time vs. Temperature

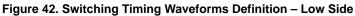
TYPICAL CHARACTERISTICS (Continued)

TYPICAL CHARACTERISTICS (Continued)









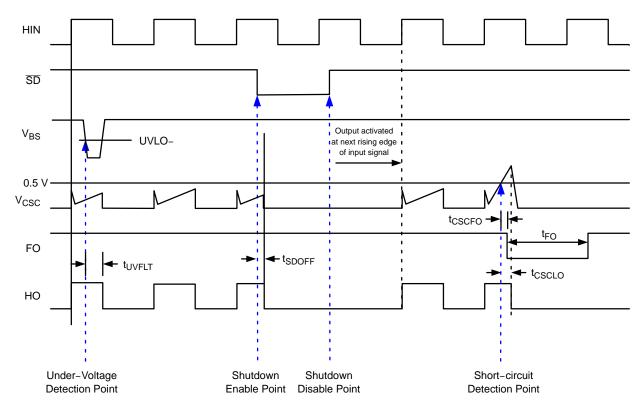


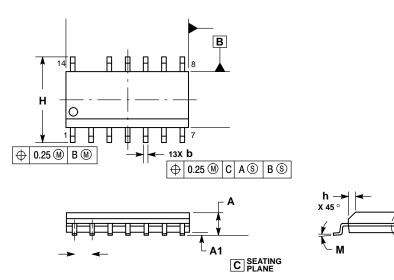
Figure 43. Switching Timing Waveforms Definition – High Side



SOIC 14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

SIDE.

GENERIC **MARKING DIAGRAM***

14	A	Ħ	Ħ	Ħ	A	A	<u> </u>
		xx	хх	хх	хх	XG	
	0	A	٩W	LY۱	NΝ	/	
1	H	H	H	H	H	H	Ъ

XXXXX	= Specific Device Code
A	= Assembly Location
WL	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb-Free Package

STYLES ON PAGE 2

DATE 03 FEB 2016

STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE

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